

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI TVV014** is Designed for

FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	10 A
V_{CB}	60 V
V_{CE}	35 V
P_{DISS}	140 W
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.5 °C/W

PACKAGE STYLE .500 6L FLG

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.150 / 3.43	.160 / 4.06
B	.045 / 1.14	
C	.210 / 5.33	.220 / 5.59
D	.835 / 21.21	.865 / 21.97
E	.200 / 5.08	.210 / 5.33
F	.490 / 12.45	.510 / 12.95
G	.003 / 0.08	.007 / 0.18
H	.125 / 3.18	
I	.725 / 18.42	
J	.970 / 24.64	.980 / 24.89
K	.090 / 2.29	.105 / 2.67
L	.150 / 3.81	.170 / 4.32
M	.285 / 7.24	
N	.120 / 3.05	.135 / 3.43

ORDER CODE: ASI10657

CHARACTERISTICS $T_C = 25^\circ\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CEO}	I _C = 50 mA			35			V
BV_{CER}	I _C = 50 mA	R _{BE} = 10 Ω		60			V
BV_{EBO}	I _E = 10 mA			4.0			V
I_{CES}	V _E = 28 V					5	mA
h_{FE}	V _{CE} = 5.0 V	I _C = 1.0 A		10		100	---
C_{ob}	V _{CB} = 28 V	f = 1.0 MHz				80	pF
P_{GE}	V _{CE} = 25 V	I _{CQ} = 3.2 A	f = 225 MHz	13.5	14.5		dB
IMD₃	P _{REF} = 16 W	Vision = -8 dB Side Band = -16 dB	Snd. = -7 dB			-55	dBc